

L Number	Hits	Search Text	DB	Time stamp
29	27002	((chemical near5 mechanical near5 polish\$3) CMP)	USPAT; US-PGPUB	2003/05/28 19:05
30	12626	((chemical near5 mechanical near5 polish\$3) CMP)) and ((insulat\$3 dielectric oxide) and planar\$6 and (conduct\$6 polysilicon))	USPAT; US-PGPUB	2003/05/28 19:06
31	8056	((((chemical near5 mechanical near5 polish\$3) CMP)) and ((insulat\$3 dielectric oxide) and planar\$6 and (conduct\$6 polysilicon))) and selectiv\$6	USPAT; US-PGPUB	2003/05/28 19:06
36	4447	(((((chemical near5 mechanical near5 polish\$3) CMP)) and ((insulat\$3 dielectric oxide) and planar\$6 and (conduct\$6 polysilicon))) and selectiv\$6) and rate	USPAT; US-PGPUB	2003/05/28 18:36
37	3681	(((((chemical near5 mechanical near5 polish\$3) CMP)) and ((insulat\$3 dielectric oxide) and planar\$6 and (conduct\$6 polysilicon))) and selectiv\$6) and rate) and (first near5 (layer material film))	USPAT; US-PGPUB	2003/05/28 18:37
38	3488	((((((chemical near5 mechanical near5 polish\$3) CMP)) and ((insulat\$3 dielectric oxide) and planar\$6 and (conduct\$6 polysilicon))) and selectiv\$6) and rate) and (second near5 (layer material film))	USPAT; US-PGPUB	2003/05/28 18:38
39	1588	((((((chemical near5 mechanical near5 polish\$3) CMP)) and ((insulat\$3 dielectric oxide) and planar\$6 and (conduct\$6 polysilicon))) and selectiv\$6) and rate) and (third near5 (layer material film))	USPAT; US-PGPUB	2003/05/28 18:39
40	3298	((((((chemical near5 mechanical near5 polish\$3) CMP)) and ((insulat\$3 dielectric oxide) and planar\$6 and (conduct\$6 polysilicon))) and selectiv\$6) and rate) and (first near5 (layer material film)) and (((((chemical near5 mechanical near5 polish\$3) CMP)) and ((insulat\$3 dielectric oxide) and planar\$6 and (conduct\$6 polysilicon))) and selectiv\$6) and rate)	USPAT; US-PGPUB	2003/05/28 18:40
41	1526	((((((chemical near5 mechanical near5 polish\$3) CMP)) and ((insulat\$3 dielectric oxide) and planar\$6 and (conduct\$6 polysilicon))) and selectiv\$6) and rate) and (first near5 (layer material film)) and (((((chemical near5 mechanical near5 polish\$3) CMP)) and ((insulat\$3 dielectric oxide) and planar\$6 and (conduct\$6 polysilicon))) and selectiv\$6) and rate) and (second near5 (layer material film)) and (((((chemical near5 mechanical near5 polish\$3) CMP)) and ((insulat\$3 dielectric oxide) and planar\$6 and (conduct\$6 polysilicon))) and selectiv\$6) and rate) and (third near5 (layer material film))	USPAT; US-PGPUB	2003/05/28 18:41
42	9426	((chemical near5 mechanical near5 polish\$3) CMP)	EPO; JPO; DERWENT; IBM_TDB	2003/05/28 19:06
43	409	((chemical near5 mechanical near5 polish\$3) CMP)) and ((insulat\$3 dielectric oxide) and planar\$6 and (conduct\$6 polysilicon))	EPO; JPO; DERWENT; IBM_TDB	2003/05/28 19:06